

MA3X701

Silicon epitaxial planar type

For high-frequency rectification

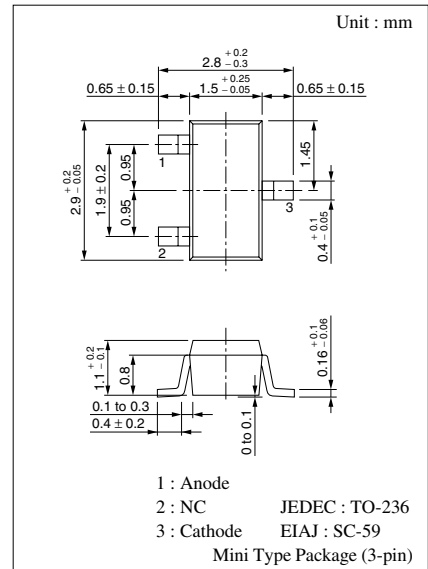
■ Features

- Mini type 3-pin package
- Allowing to rectify under ($I_{F(AV)} = 700$ mA) condition

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

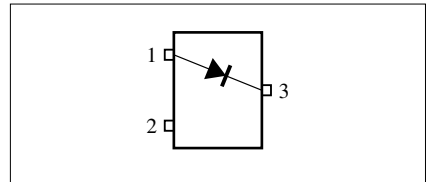
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	30	V
Repetitive peak reverse voltage	V_{RRM}	30	V
Average forward current	$I_{F(AV)}$	700	mA
Non-repetitive peak forward surge current*	I_{FSM}	5	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) * : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)



Marking Symbol: M4P

Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 30$ V			80	μA
Forward voltage (DC)	V_F	$I_Z = 700$ mA			0.55	V
Terminal capacitance	C_t	$V_R = 0$ V, $f = 1$ MHz		120		pF
Reverse recovery time*2	t_{rr}	$I_F = I_R = 100$ mA $I_{rr} = 10$ mA, $R_L = 100$ Ω		7.5		ns
Thermal resistance (1)	$R_{th(j-a)(1)}$			420		$^\circ\text{C/W}$
Thermal resistance (2)*1	$R_{th(j-a)(2)}$			330		$^\circ\text{C/W}$

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

2. Rated input/output frequency: 400 MHz

3. *1 : Obtained by fixing the element to the printed-circuit board (copper foil area 0.8 mm × 20 mm)

*2 : t_{rr} measuring circuit

